# Abstracts

## 30 dB of AGC from an FET

*B.R. Hallford. "30 dB of AGC from an FET." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 613-616.*

A low-noise single-gate GaAs MESFET has been successfully used to provide a 30-dB AGC range for low-noise amplifiers in down-converters used in microwave communication systems from 4 to 11 GHz. Threshold NF is not affected. With 30 dB of AGC, the FET amplifier NF is 18 dB.

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